TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2401

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & \vdots\ R_{DS}\ (on) = 0.13\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & \vdots\ |Y_{fs}| = 17\ S\ (typ.) \\ \bullet & Low\ leakage\ current & \vdots\ I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 200\ V) \\ \bullet & Enhancement-mode & \vdots\ V_{th} = 1.5 \\ \sim 3.5\ V\ (V_{DS} = 10\ V,\ I_D = 1\ mA) \end{array}$

Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	200	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	200	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	15	Α	
	Pulse (Note 1)	I _{DP}	45	Α	
Drain power dissipatio	n (Tc = 25°C)	P _D	75	W	
Single pulse avalanche energy (Note 2)		E _{AS}	166	mJ	
Avalanche current		I _{AR}	15	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	7.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.67	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

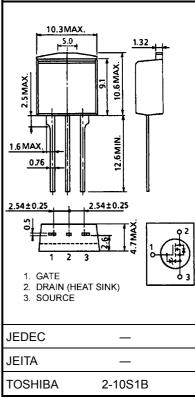
Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.2 mH, R_G = 25 Ω , I_{AR} = 15 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

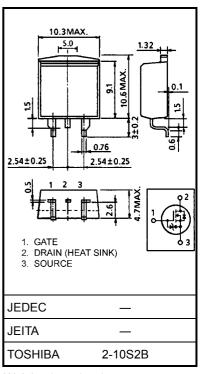
This transistor is an electrostatic sensitive device.

Please handle with caution.





Weight: 1.5 g (typ.)



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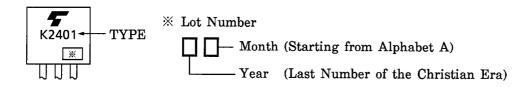
Electrical Characteristics (Ta = 25°C)

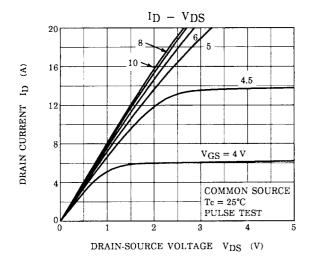
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μA
Drain cut-off cui	rent	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V		_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	200	_	_	V
Gate threshold v	roltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source Ol	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 10 A	-	0.13	0.18	Ω
Forward transfer	admittance	Y _{fS}	V _{DS} = 10 V, I _D = 10 A	10	17	_	S
Input capacitano	е	C _{iss}		_	2000	_	
Reverse transfer	capacitance	C _{rss}			200	_	pF
Output capacitar	nce	C _{oss}			600	_	
Switching time	Rise time	t _r	$V_{GS} \stackrel{10 \text{ V}}{\text{0 V}} \stackrel{\text{I}_{D} = 10 \text{ A}}{\text{0 V}_{out}}$ $R_{L} = 10 \Omega$ $V_{DD} = 100 \text{ V}$	_	35	1	- ns
	Turn-on time	t _{on}		_	50	_	
	Fall time	t _f		_	10	_	
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \ \mu s$	_	66	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	40	-	
Gate-source charge		Q _{gs}	$V_{DD} \approx 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		25	_	nC
Gate-drain ("miller") charge		Q_{gd}			15	_	

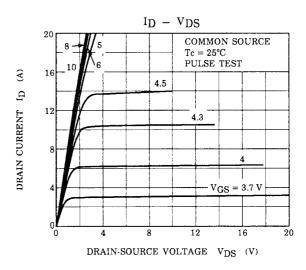
Source-Drain Ratings and Characteristics (Ta = 25°C)

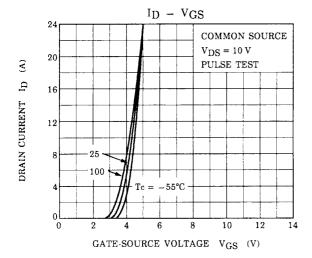
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	15	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	45	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 15 A, V _{GS} = 0 V	_	_	-2.0	V
Reverse recovery time	t _{rr}	I _{DR} = 15 A, V _{GS} = 0 V	1	180	-	ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs		1.13	_	μC

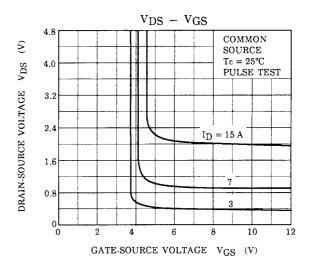
Marking

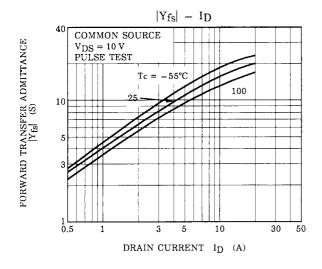


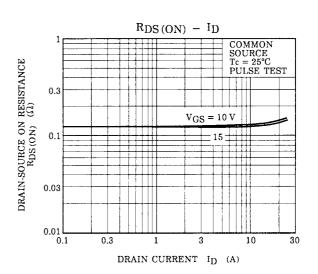




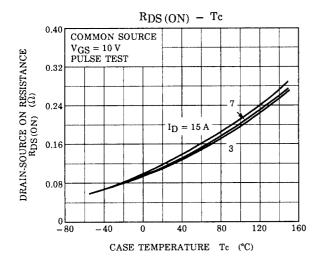


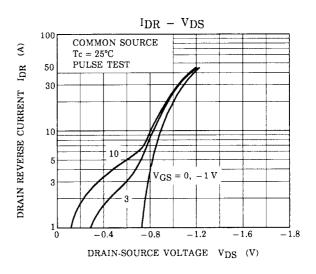


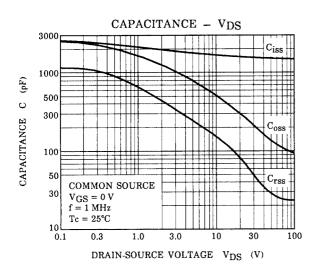


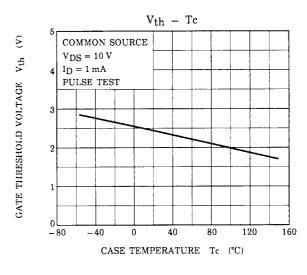


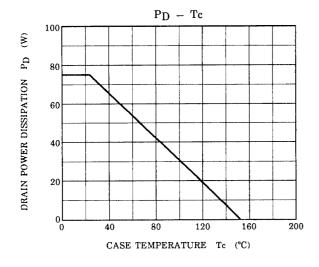
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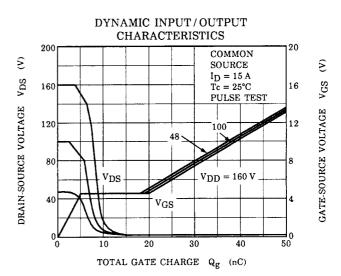




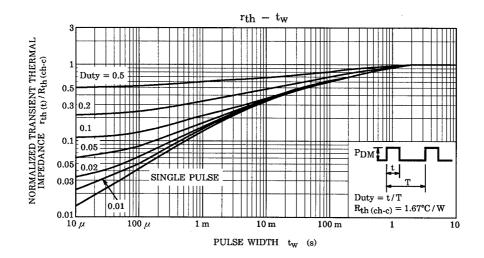


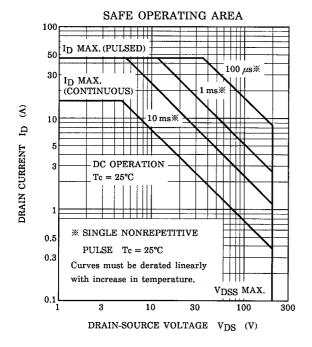


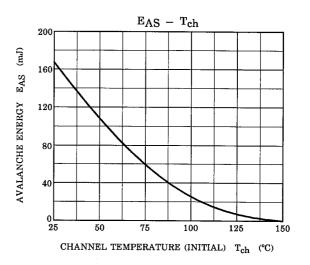


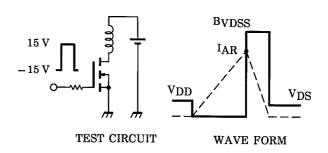


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$$\begin{aligned} &R_G = 25~\Omega \\ &V_{DD} = 50~V,~L = 1.2~mH \end{aligned} \qquad EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD}\right) \end{aligned}$$

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